

FSS139

 — P-Channel Silicon MOSFET

Load Switching Applications

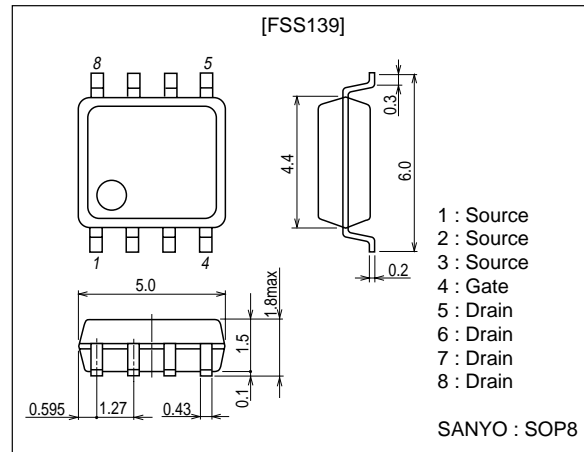
Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Package Dimensions

unit : mm

2116



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-20	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		-4	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-48	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (1200mm²×0.8mm)	1.8	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =-1mA, V _{GS} =0	-20			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-0.4		-1.4	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-4A	6.3	9		S

Marking : S139

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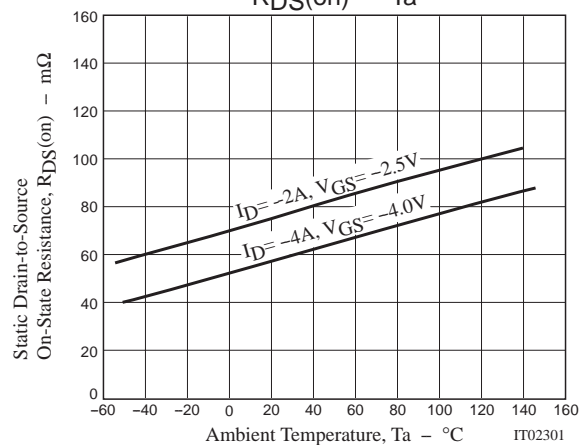
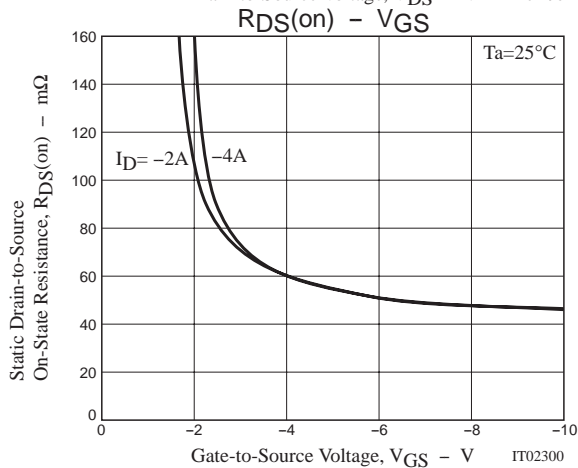
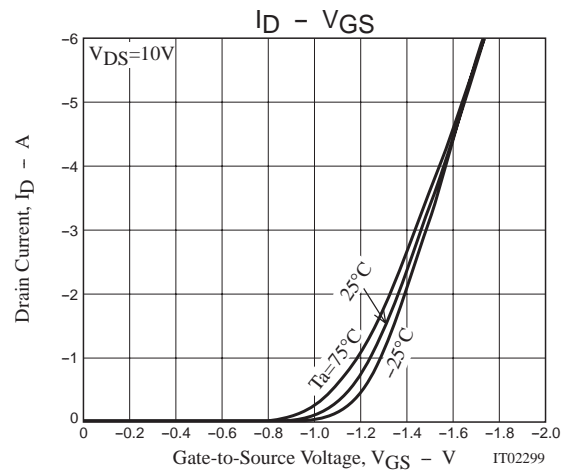
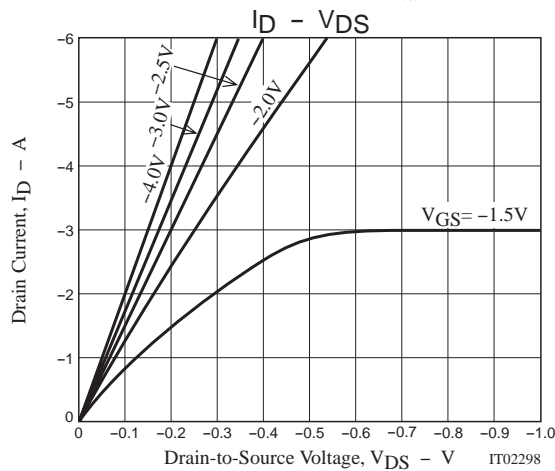
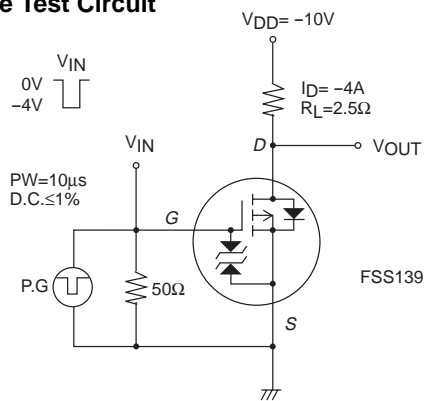
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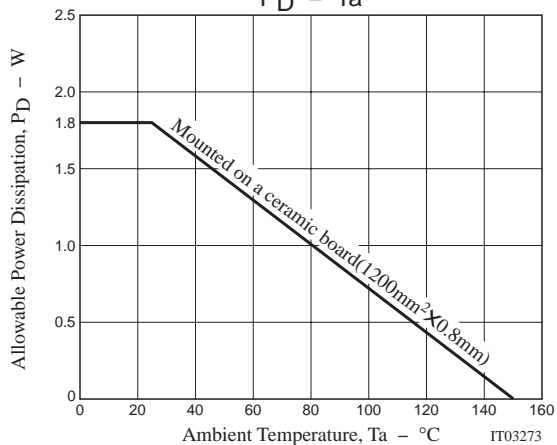
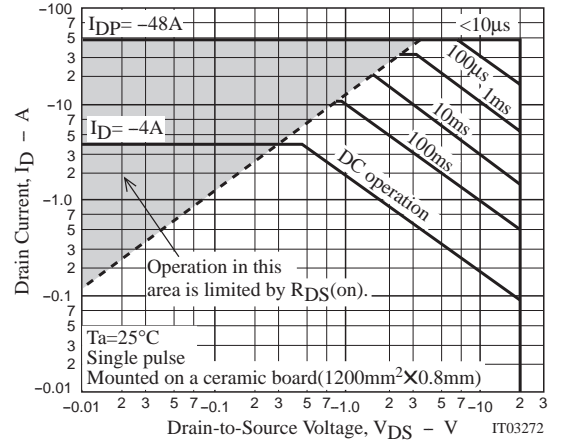
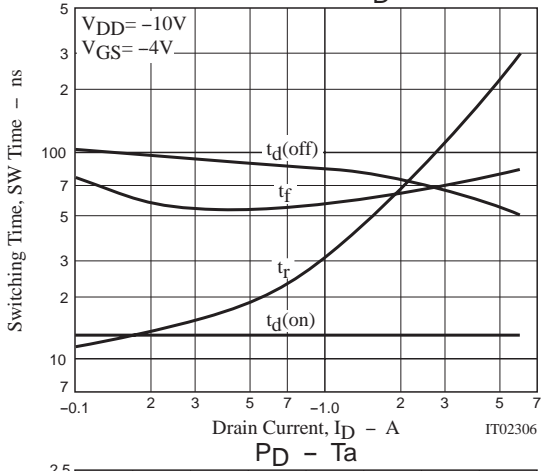
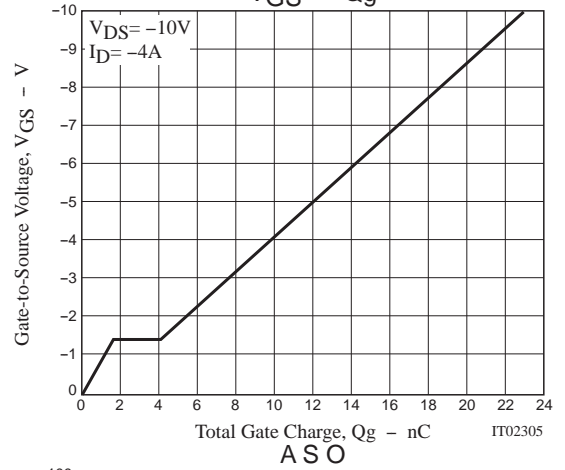
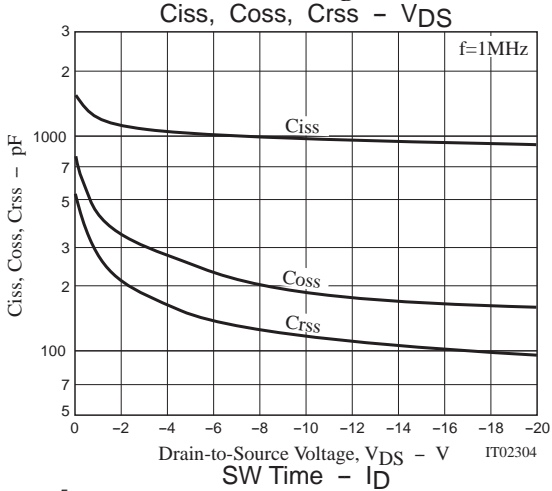
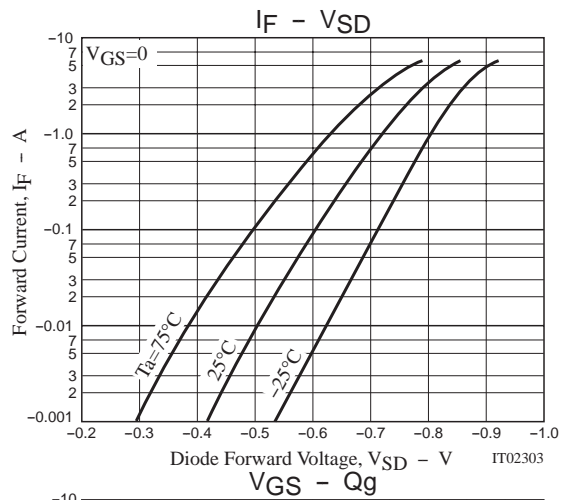
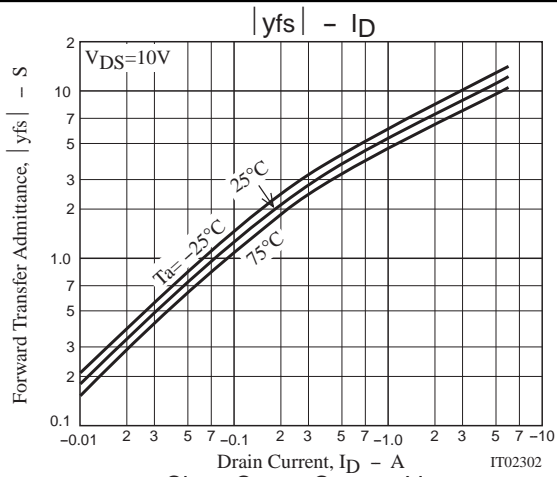
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Static Drain-to-Source On-State Resistance	$R_{DS(on) 1}$	$I_D = -4A, V_{GS} = -4V$		60	78	m Ω
	$R_{DS(on) 2}$	$I_D = -2A, V_{GS} = -2.5V$		78	110	m Ω
Input Capacitance	C_{iss}	$V_{DS} = -10V, f = 1MHz$		1000		pF
Output Capacitance	C_{oss}	$V_{DS} = -10V, f = 1MHz$		190		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -10V, f = 1MHz$		120		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit		13		ns
Rise Time	t_r	See specified Test Circuit		200		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit		52		ns
Fall Time	t_f	See specified Test Circuit		78		ns
Total Gate Charge	Q_g	$V_{DS} = -10V, V_{GS} = -10V, I_D = -4A$		23		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS} = -10V, V_{GS} = -10V, I_D = -4A$		1.6		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS} = -10V, V_{GS} = -10V, I_D = -4A$		2.3		nC
Diode Forward Voltage	V_{SD}	$I_S = -4A, V_{GS} = 0$		-0.89	-1.5	V

Switching Time Test Circuit





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